

## HAT1043M

Silicon P Channel Power MOS FET  
Power Switching

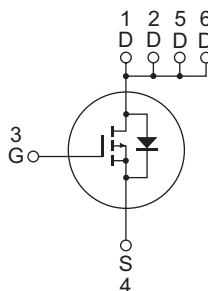
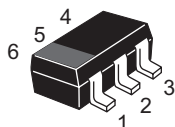
REJ03G1151-0600  
(Previous: ADE-208-754D)  
Rev.6.00  
Sep 07, 2005

### Features

- Low on-resistance
- Low drive current
- High density mounting
- 2.5 V gate drive device can be driven from 3 V source

### Outline

RENESAS Package code: PTSP0006FA-A  
(Package name: TSOP-6)



4 Source  
3 Gate  
1, 2, 5, 6 Drain

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V <sub>DSS</sub>	-20	V
Gate to source voltage	V <sub>GSS</sub>	±12	V
Drain current	I <sub>D</sub>	-4.4	A
Drain peak current	I <sub>D (pulse)</sub> <sup>Note 1</sup>	-17.6	A
Body-drain diode reverse drain current	I <sub>DR</sub> <sup>Note 2</sup>	-4.4	A
Channel dissipation	P <sub>ch (pulse)</sub> <sup>Note 2</sup>	2.0	W
Channel dissipation	P <sub>ch (continuous)</sub> <sup>Note 3</sup>	1.05	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%

2. When using the alumina ceramic board (50 × 50 × 0.7 mm), PW ≤ 5 s, Ta = 25°C

3. When using the alumina ceramic board (50 × 50 × 0.7 mm), Ta = 25°C

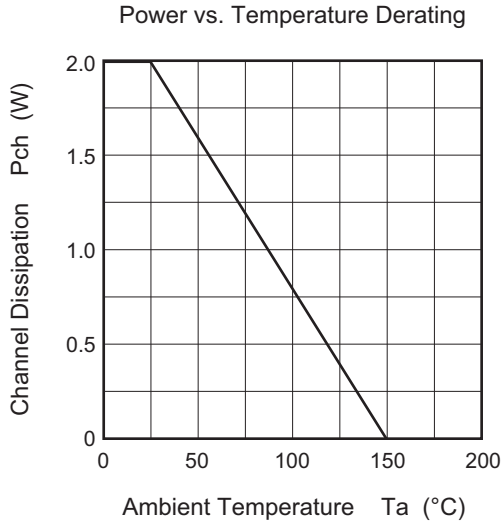
## Electrical Characteristics

(Ta = 25°C)

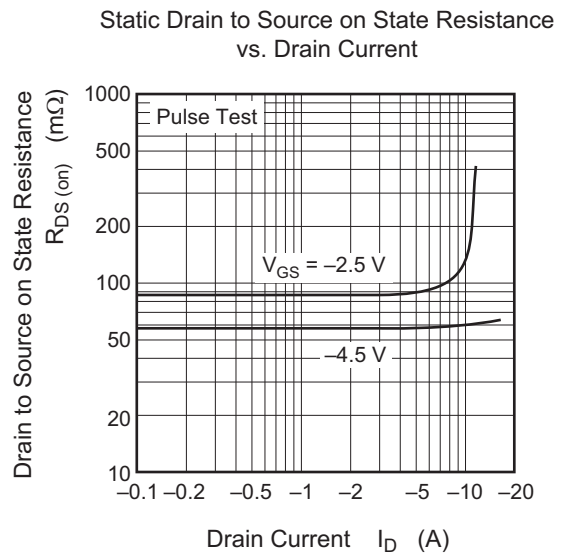
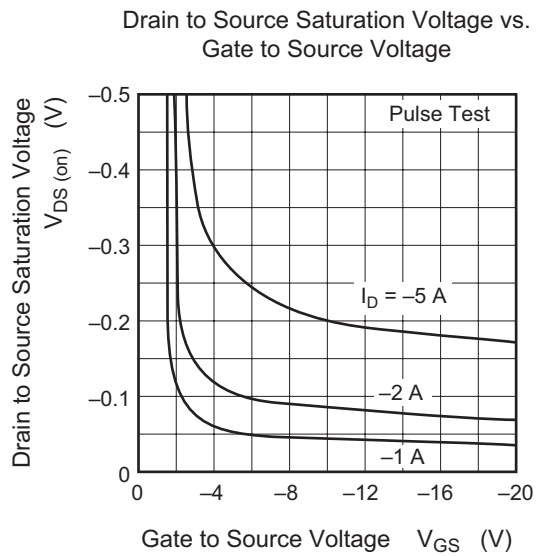
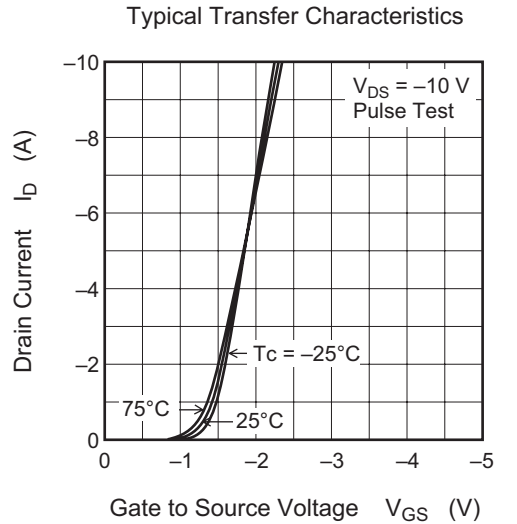
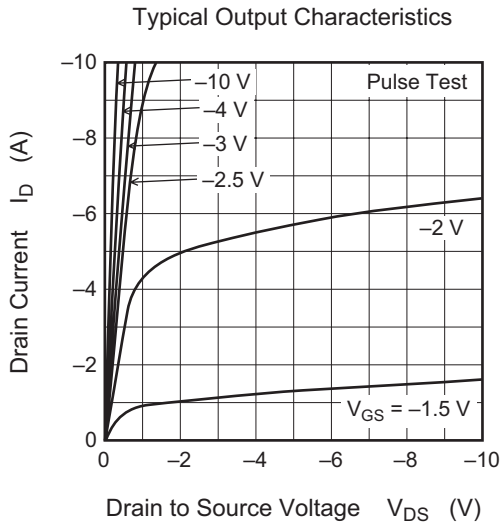
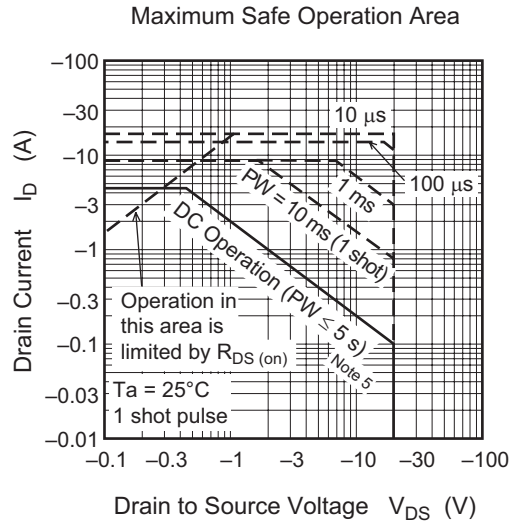
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR) DSS</sub>	-20	—	—	V	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	—	—	±0.1	μA	V <sub>GS</sub> = ±12 V, V <sub>DS</sub> = 0
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	-1	μA	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0
Gate to source cutoff voltage	V <sub>GS (off)</sub>	-0.4	—	-1.4	V	I <sub>D</sub> = -1 mA, V <sub>DS</sub> = -10 V
Static drain to source on state resistance	R <sub>DS (on)</sub>	—	55	65	mΩ	I <sub>D</sub> = -3 A, V <sub>GS</sub> = -4.5 V <sup>Note 4</sup>
	R <sub>DS (on)</sub>	—	85	110	mΩ	I <sub>D</sub> = -3 A, V <sub>GS</sub> = -2.5 V <sup>Note 4</sup>
Forward transfer admittance	y <sub>fs</sub>	4	7	—	S	I <sub>D</sub> = -3 A, V <sub>DS</sub> = -10 V <sup>Note 4</sup>
Input capacitance	C <sub>iss</sub>	—	750	—	pF	V <sub>DS</sub> = -10 V V <sub>GS</sub> = 0 f = 1 MHz
Output capacitance	C <sub>oss</sub>	—	310	—	pF	
Reverse transfer capacitance	C <sub>rss</sub>	—	220	—	pF	
Total gate charge	Q <sub>g</sub>	—	11	—	nC	V <sub>DD</sub> = -10 V
Gate to source charge	Q <sub>gs</sub>	—	2	—	nC	V <sub>GS</sub> = -4.5 V
Gate to drain charge	Q <sub>gd</sub>	—	3.5	—	nC	I <sub>D</sub> = -4.4 A
Turn-on delay time	t <sub>d (on)</sub>	—	15	—	ns	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -3 A, R <sub>L</sub> = 3.3 Ω
Rise time	t <sub>r</sub>	—	100	—	ns	
Turn-off delay time	t <sub>d (off)</sub>	—	85	—	ns	
Fall time	t <sub>f</sub>	—	100	—	ns	
Body-drain diode forward voltage	V <sub>DF</sub>	—	-0.95	-1.23	V	I <sub>F</sub> = -4.4 A, V <sub>GS</sub> = 0
Body-drain diode reverse recovery time	t <sub>rr</sub>	—	50	—	ns	I <sub>F</sub> = -4.4 A, V <sub>GS</sub> = 0 di <sub>F</sub> /dt = -20 A/μs

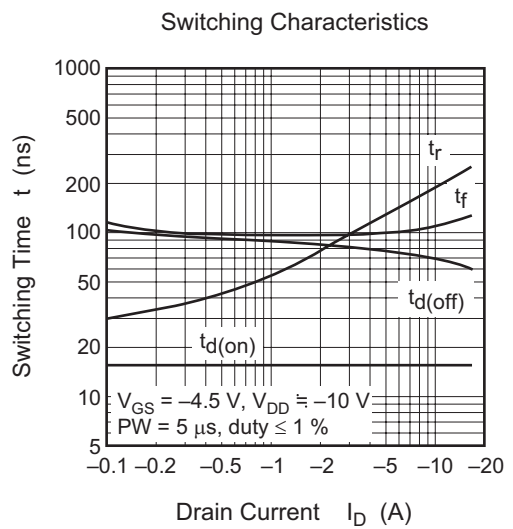
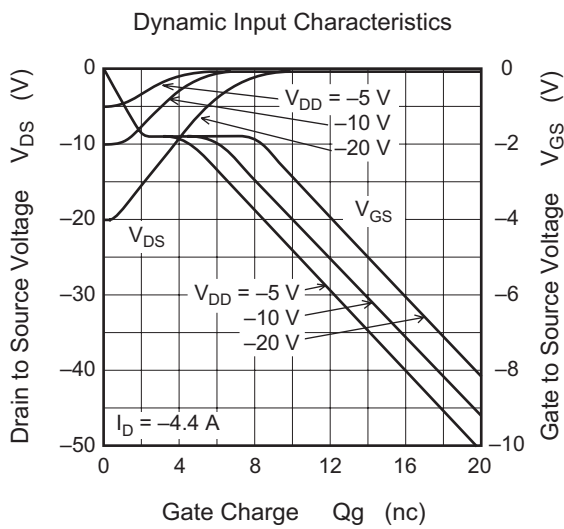
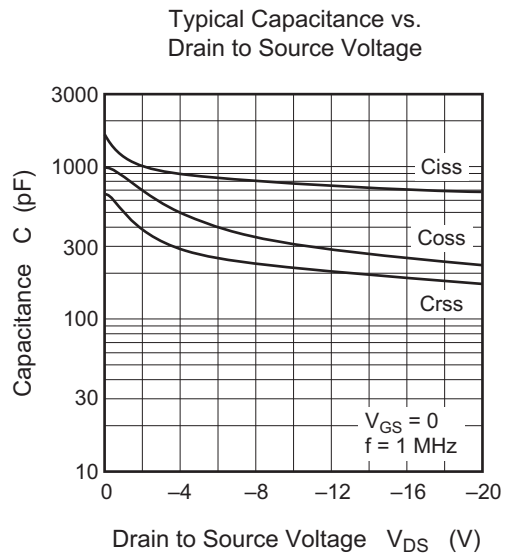
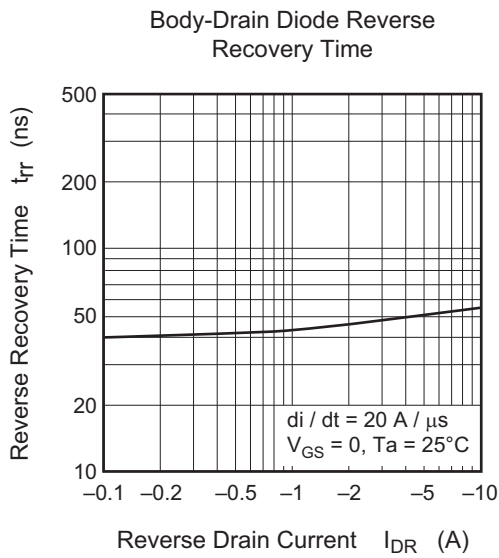
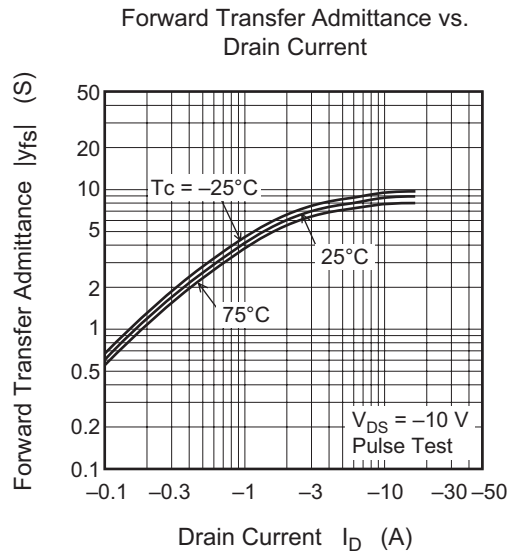
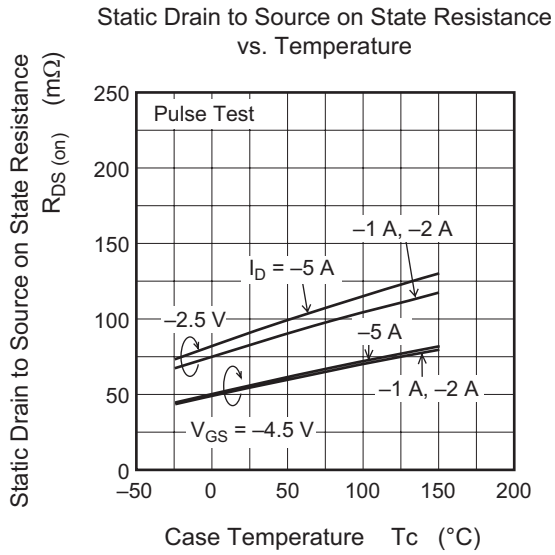
Note: 4. Pulse test

Main Characteristics

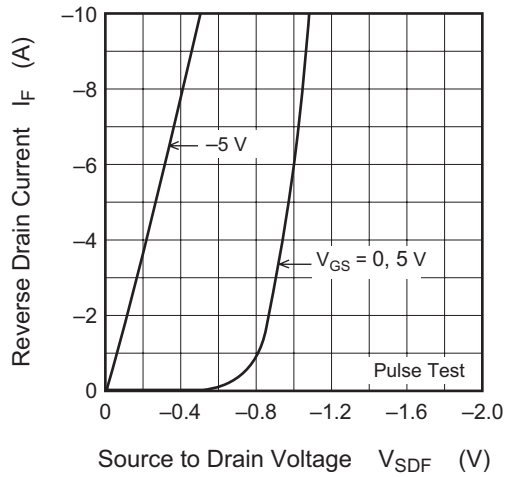


Test Condition:  
When using the alumina ceramic board  
(50 × 50 × 0.7 mm), ( $PW \leq 5$  s)

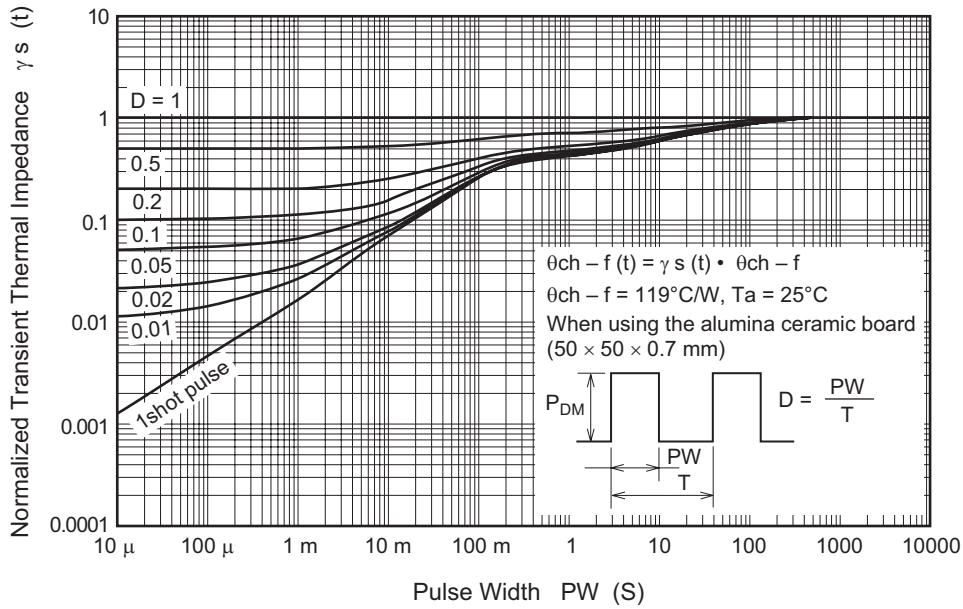




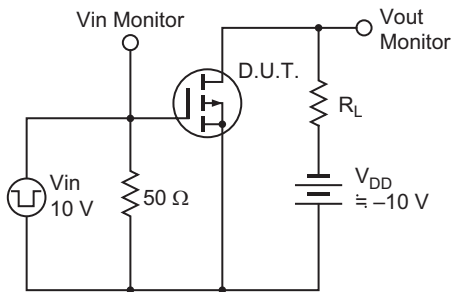
Reverse Drain Current vs. Source to Drain Voltage



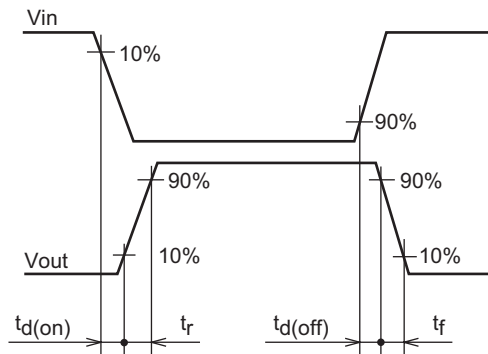
Normalized Transient Thermal Impedance vs. Pulse Width



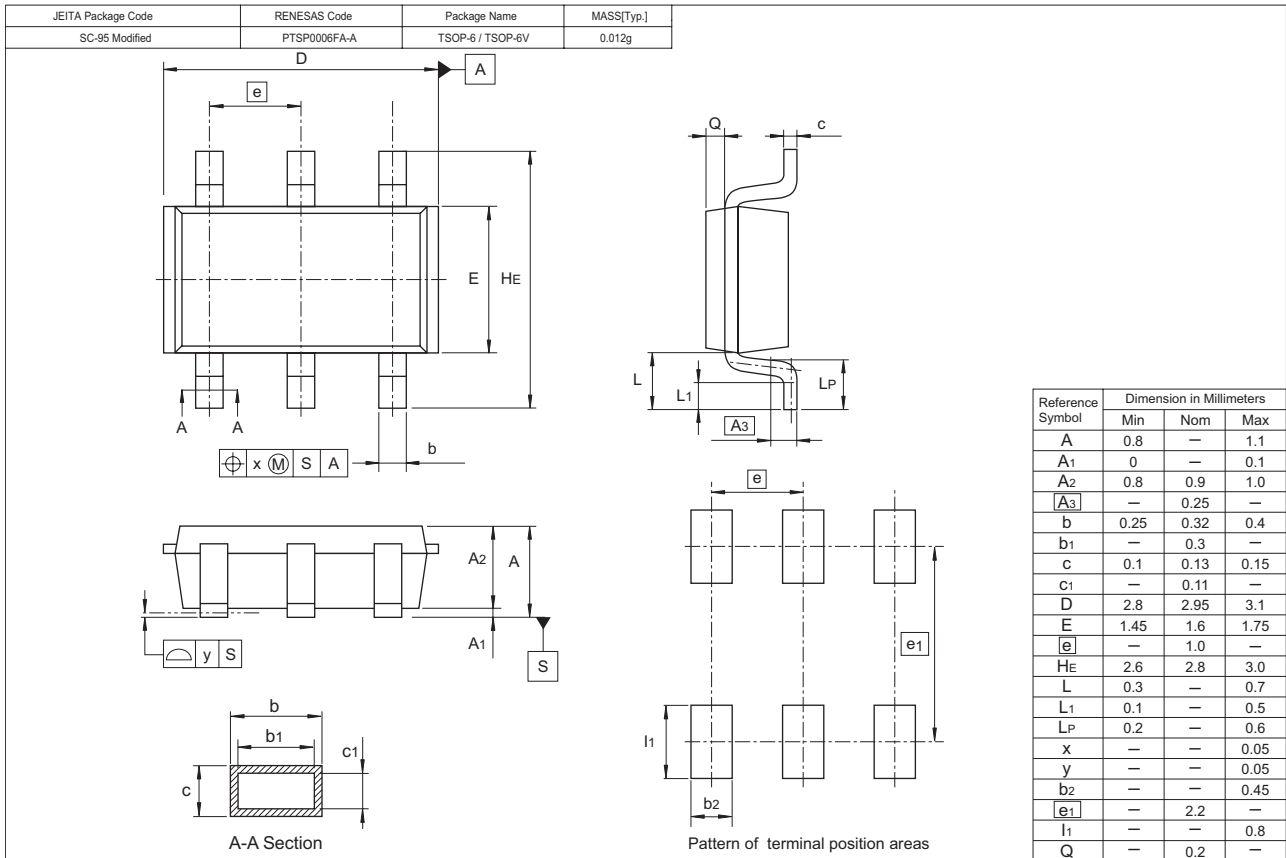
Switching Time Test Circuit



Switching Time Waveform



### Package Dimensions



### Ordering Information

Part Name	Quantity	Shipping Container
HAT1043M-EL-E	3000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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